

XN4503

Silicon NPN epitaxial planer transistor

For amplification of low frequency output

Features

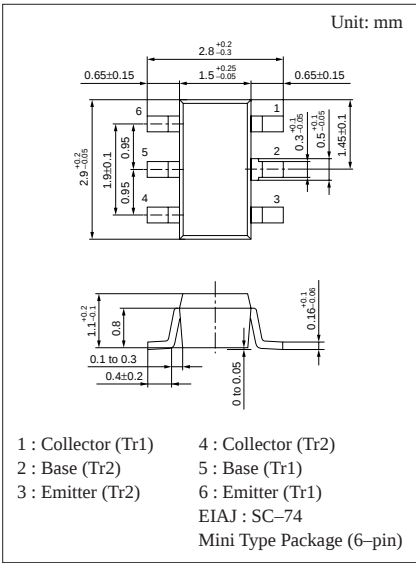
- Two elements incorporated into one package.
- Reduction of the mounting area and assembly cost by one half.

Basic Part Number of Element

- 2SD813 × 2 elements

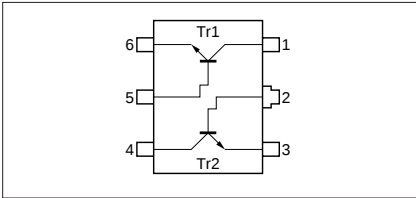
Absolute Maximum Ratings (Ta=25°C)

	Parameter	Symbol	Ratings	Unit
Rating of element	Collector to base voltage	V_{CBO}	25	V
	Collector to emitter voltage	V_{CEO}	20	V
	Emitter to base voltage	V_{EBO}	7	V
	Collector current	I_C	0.5	A
	Peak collector current	I_{CP}	1	A
Overall	Total power dissipation	P_T	300	mW
	Junction temperature	T_j	150	°C
	Storage temperature	T_{sig}	-55 to +150	°C



Marking Symbol: 5Y

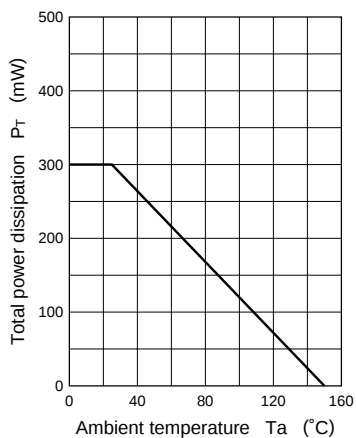
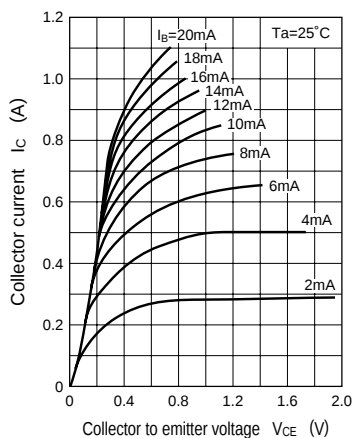
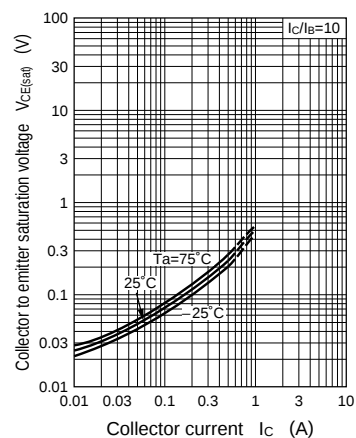
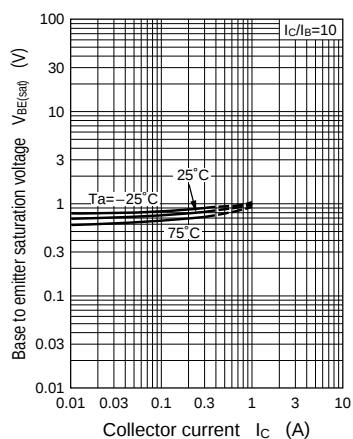
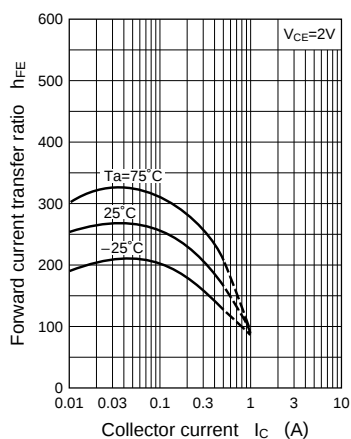
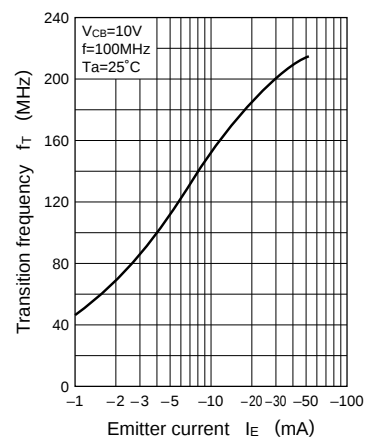
Internal Connection



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V_{CBO}	$I_C = 10\mu A, I_E = 0$	25			V
Collector to emitter voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	20			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	7			V
Collector cutoff current	I_{CBO}	$V_{CB} = 25V, I_E = 0$			0.1	μA
	I_{CEO}	$V_{CE} = 20V, I_B = 0$			1	μA
Forward current transfer ratio	h_{FE1}	$V_{CE} = 2V, I_C = 500mA^*$	65		350	
	h_{FE2}	$V_{CE} = 2V, I_C = 1A^*$	50			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 20mA^*$		0.2	0.4	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500mA, I_B = 50mA^*$			1.2	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -50mA, f = 200MHz$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		6		pF

* Pulse measurement

$P_T - T_a$  $I_C - V_{CE}$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$ 